WHAT IS CLAIMED IS:

1. An insulating paste for an electronic device comprising Si particles and an organic Si compound.

2. The insulating paste of Claim 1, wherein the organic Si compound reacts with the Si particles to form a Si-O bond.

3. The insulating paste of Claim 1, which further comprises insulating particles and wherein the organic Si compound reacts with the Si particles to form a Si-O bond around the insulating particles.

4. The insulating paste of Claim 1, wherein the organic Si compound is either alkylalkoxysilane or organopolysiloxane (alkoxysilane having a functional side chain).

5. The insulating paste of Claim 2, wherein the organic Si compound is either alkylalkoxysilane or organopolysiloxane (alkoxysilane having a functional side chain).

6. The insulating paste of Claim 3, wherein the organic Si compound is either alkylalkoxysilane or organopolysiloxane (alkoxysilane having a functional side chain).

7. An electronic device having an insulator in a minute space, wherein the insulator is formed with the insulating paste of Claim 1.

8. An electronic device having an insulator in a minute space, wherein

the insulator is formed with the insulating paste of Claim 2.

9. An electronic device having an insulator in a minute space, wherein the insulator is formed with the insulating paste of Claim 3.

10. An electronic device having an insulator in a minute space, wherein the insulator is formed with the insulating paste of Claim 4.

11. An electronic device having an insulator in a minute space, wherein the insulator is formed with the insulating paste of Claim 5.

12. An electronic device having an insulator in a minute space, wherein the insulator is formed with the insulating paste of Claim 6.

13. A method for forming an insulator in a minute space of an electronic device, comprising the steps of:

pouring a paste containing insulating particles, Si particles and an organic Si compound into the minute space; and

then, reacting the organic Si compound with the Si particles by heat treatment to form a Si-O bond filling up a space around the insulating particles.

14. A method for forming an insulator in a minute space of an electronic device, comprising the steps of:

pouring a silicon oil into the minute space and forming Si particles by heat treatment;

pouring a paste containing insulating particles and an organic Si

compound into the minute space; and

then, reacting the organic Si compound with the Si particles by heat treatment to form a Si-O bond filling up a space around the insulating particles.

WHAT IS CLAIMED IS:

1. An insulating paste for an electronic device comprising Si particles and an organic Si compound.

2. The insulating paste of Claim 1, wherein the organic Si compound reacts with the Si particles to form a Si-O bond.

3. The insulating paste of Claim 1, which further comprises insulating particles and wherein the organic Si compound reacts with the Si particles to form a Si-O bond around the insulating particles.

4. The insulating paste of any of Claim 1 to 3, wherein the organic Si compound is either alkylalkoxysilane or organopolysiloxane (alkoxysilane having a functional side chain).

5. An electronic device having an insulator in a minute space, wherein the insulator is formed with the insulating paste of any of Claim 1 to 4.

6. A method for forming an insulator in a minute space of an electronic device, comprising the steps of:

pouring a paste containing insulating particles, Si particles and an organic Si compound into the minute space; and

then, reacting the organic Si compound with the Si particles by heat treatment to form a Si-O bond filling up a space around the insulating particles.

7. A method for forming an insulator in a minute space of an electronic

device, comprising the steps of:

pouring a silicon oil into the minute space and forming Si particles by heat treatment;

pouring a paste containing insulating particles and an organic Si compound into the minute space; and

then, reacting the organic Si compound with the Si particles by heat treatment to form a Si-O bond filling up a space around the insulating particles.